

Supporting information

p-type Co interstitial defects in thermoelectric skutterudite CoSb_3 due to the breakage of Sb_4 -rings

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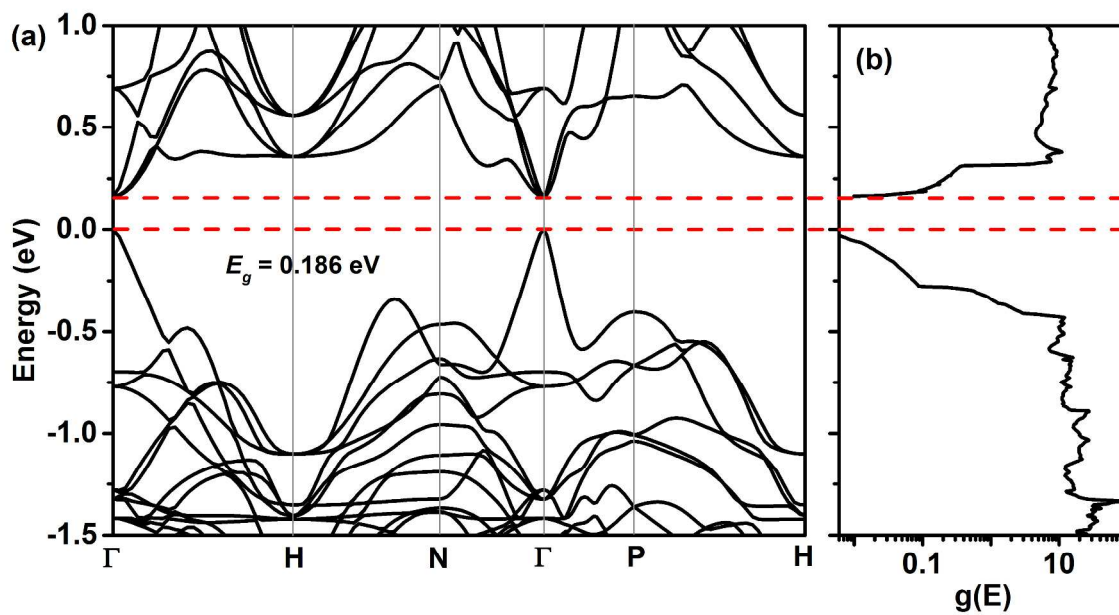


Figure S1. (a) The band structure and (b) density of state of CoSb_3 from our *ab-initio* calculation using PBE functional. The direct band gap $E_g = 0.186$ eV.

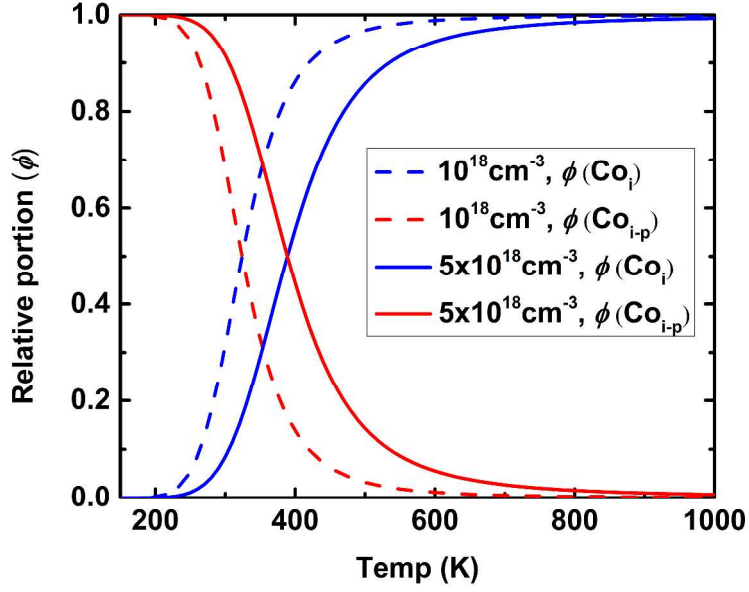


Figure S2. Relative portion of Co_i and Co_{i-p} as a function of the temperature. Solid line and dot line represent 5×10¹⁸ cm⁻³ and 10¹⁸ cm⁻³ carriers in the system respectively. The relation portion is calculated by

$$\phi = \frac{1}{1 + \exp\left(\frac{\Delta H - T\Delta S}{kT}\right)},$$

where ΔH is the formation enthalpy change between neutral Co_i and Co_{i-p}.

ΔS is the configurational entropy change defined by equation (3) in the manuscript. The defect thermodynamics calculation is time-independent.